

Features

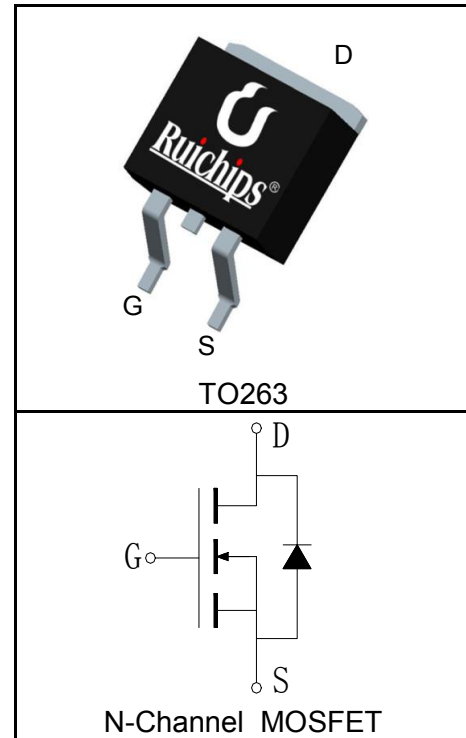
- 100V/150A,
 $R_{DS(ON)} = 3.8m\Omega(Typ.)@V_{GS}=10V$
- Advanced HEFET[®] Technology
- Ultra Low On-Resistance
- Excellent $Q_g \times R_{DS(on)}$ Product
- 100% avalanche tested
- 175°C Operating Temperature
- Lead Free and Green Devices Available (RoHS Compliant)



Applications

- Motor Drives
- Uninterruptible Power Supplies
- DC/DC converter
- General Purpose Applications

Pin Description



Absolute Maximum Ratings

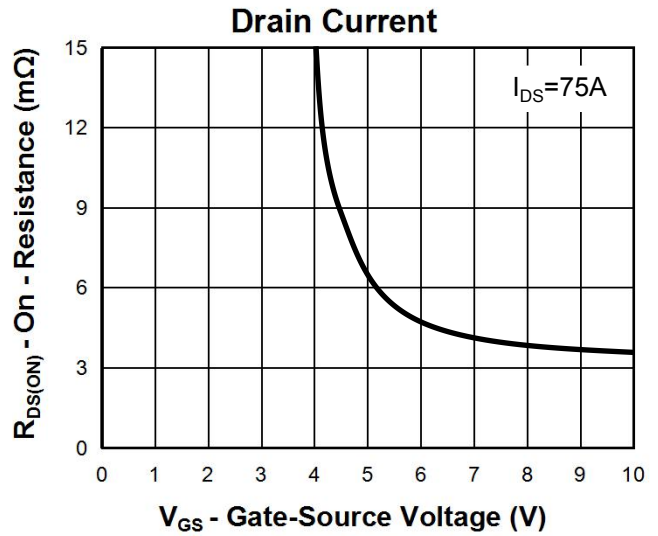
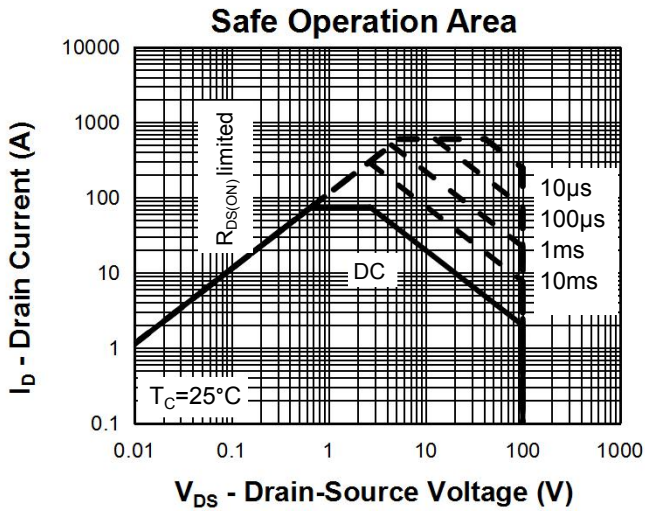
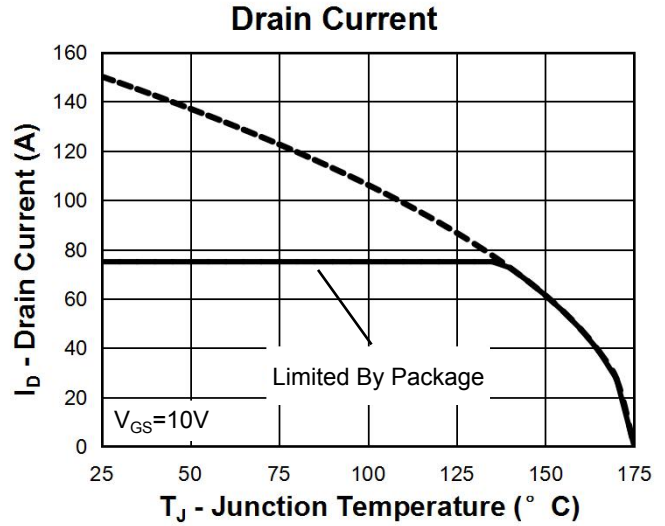
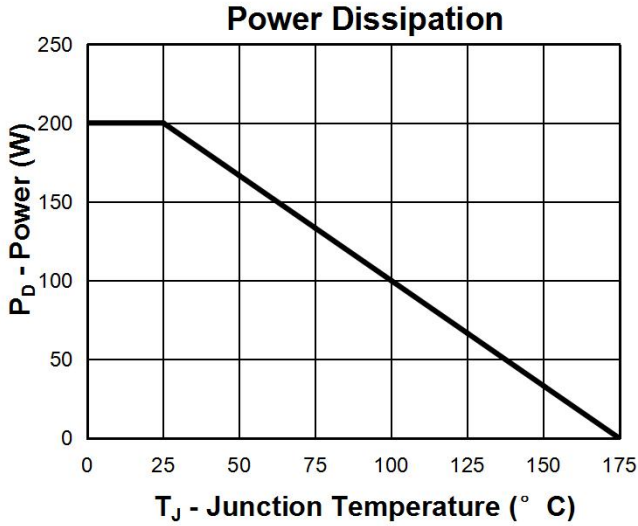
Symbol	Parameter	Rating	Unit
Common Ratings ($T_C=25^\circ C$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	± 25	
T_J	Maximum Junction Temperature	175	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
I_S	Diode Continuous Forward Current	$T_C=25^\circ C$ 150	A
Mounted on Large Heat Sink			
$I_{DP}^{①}$	300 μs Pulse Drain Current Tested	$T_C=25^\circ C$ 600	A
$I_D^{②}$	Continuous Drain Current($V_{GS}=10V$)	$T_C=25^\circ C$ 150	A
		$T_C=100^\circ C$ 106	
P_D	Maximum Power Dissipation	$T_C=25^\circ C$ 200	W
		$T_C=100^\circ C$ 100	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	0.75	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62.5	$^\circ C/W$
Drain-Source Avalanche Ratings			
$E_{AS}^{③}$	Avalanche Energy, Single Pulsed	225	mJ

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ Unless Otherwise Noted)

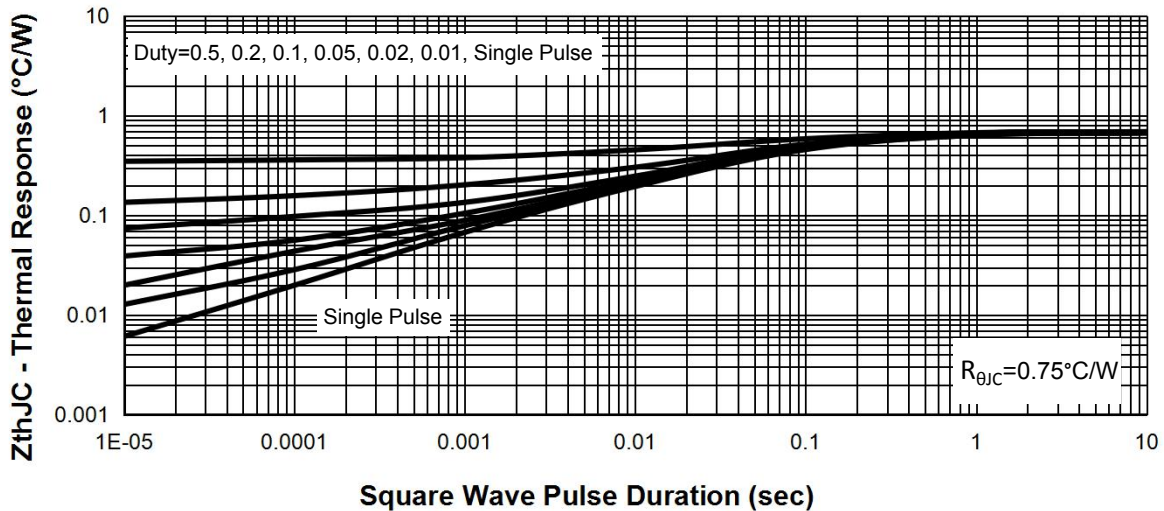
Symbol	Parameter	Test Condition	RUH1H150S			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	100			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V$			1	μA
		$T_J=125^{\circ}\text{C}$			30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2		4	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(4)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=75A$		3.8	4.5	m Ω
Diode Characteristics						
$V_{SD}^{(4)}$	Diode Forward Voltage	$I_{SD}=75A, V_{GS}=0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=75A, di_{SD}/dt=100A/\mu s$		36		ns
Q_{rr}	Reverse Recovery Charge			285		nC
Dynamic Characteristics ⁽⁵⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		2.1		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=50V,$ Frequency=1.0MHz		3650		pF
C_{oss}	Output Capacitance			750		
C_{riss}	Reverse Transfer Capacitance			27		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=50V, I_{DS}=75A,$ $V_{GEN}=10V, R_G=2.5\Omega$		24		ns
t_r	Turn-on Rise Time			13		
$t_{d(OFF)}$	Turn-off Delay Time			49		
t_f	Turn-off Fall Time			17		
Gate Charge Characteristics ⁽⁵⁾						
Q_g	Total Gate Charge	$V_{DS}=80V, V_{GS}=10V,$ $I_{DS}=75A$		87		nC
Q_{gs}	Gate-Source Charge			23		
Q_{gd}	Gate-Drain Charge			15		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 75A.
 - ③ Limited by T_{Jmax} , $I_{AS}=30A$, $V_{DD}=60V$, $R_G=50\Omega$, Starting $T_J=25^{\circ}\text{C}$.
 - ④ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑤ Guaranteed by design, not subject to production testing.

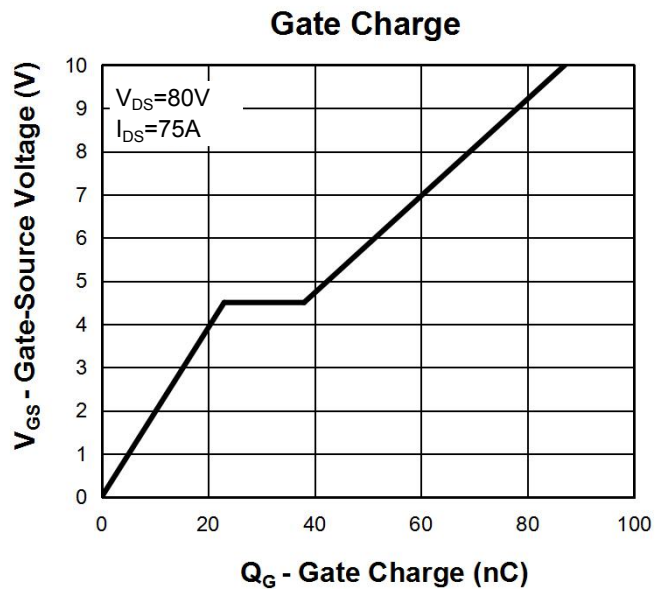
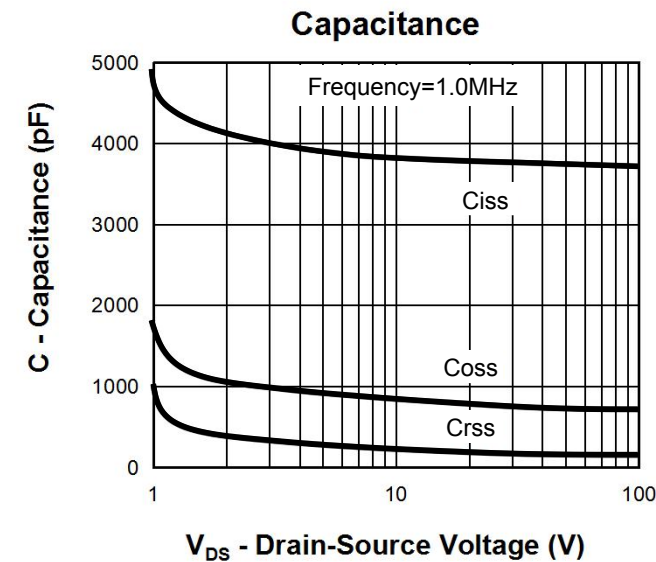
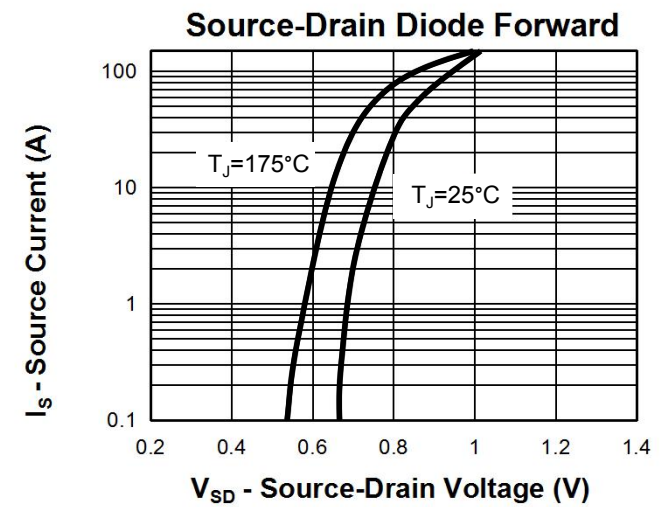
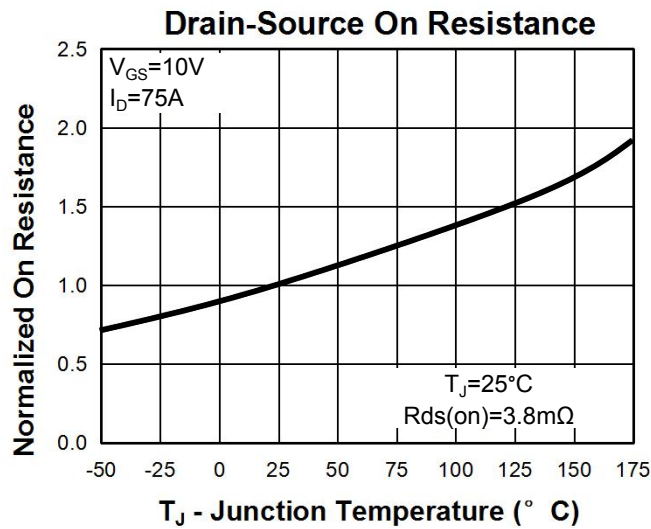
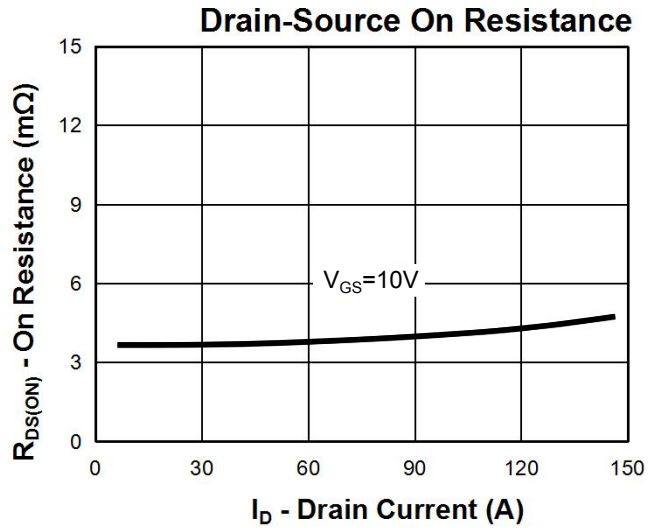
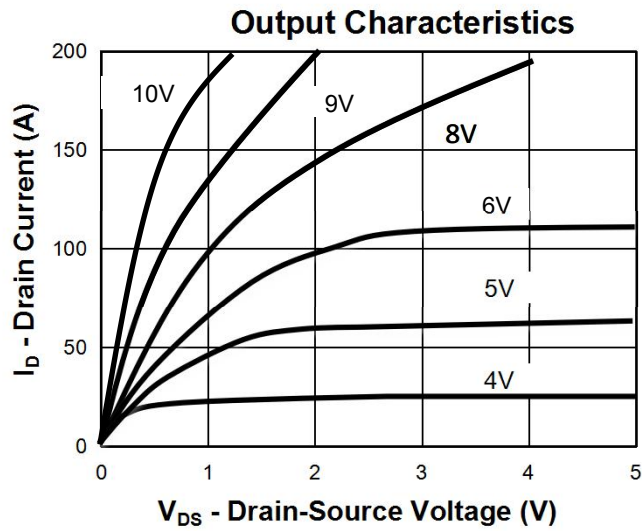
Typical Characteristics



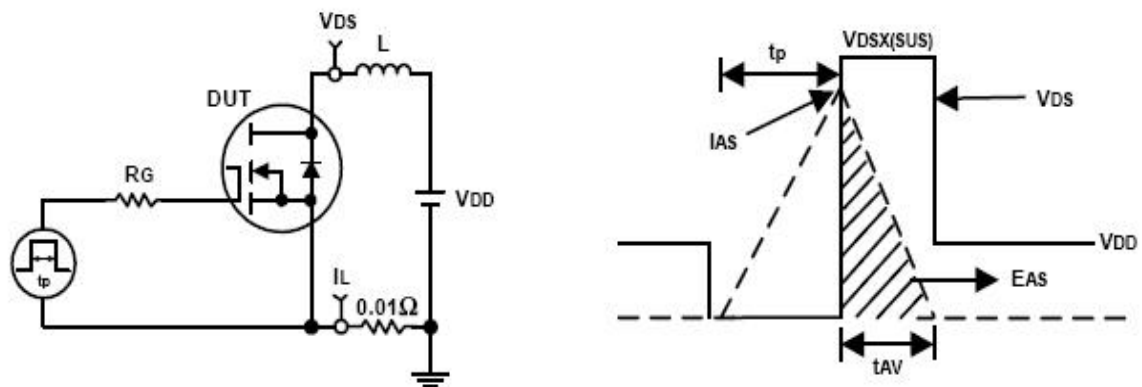
Thermal Transient Impedance



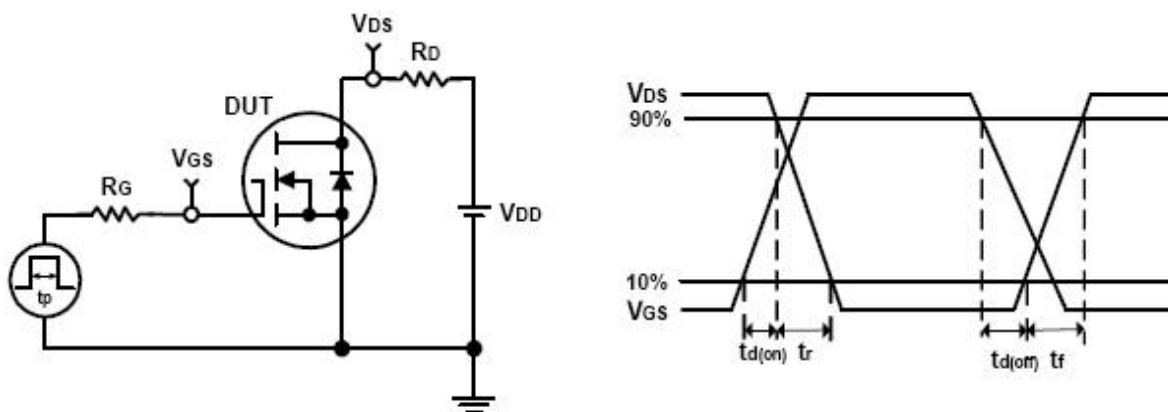
Typical Characteristics



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RUH1H150S	RUH1H150S	TO263	Tube	50	-	-
RUH1H150S-	RUH1H150S	TO263	Tape&Reel	800	13"	24mm

